2SC2229

Rev.E Mar.-2016

DATA SHEET

/ Descriptions

WR0<50P ṂṂÞ QSQ ÆṀч s ‖ ㄱ Silicon NPN transistor in a TO-92LM Plastic Package.

/ Features

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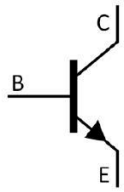
High breakdown voltage, low output capacitance, high f_T.

/ Applications

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TV video output, high voltage switching and driver stage of audio amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

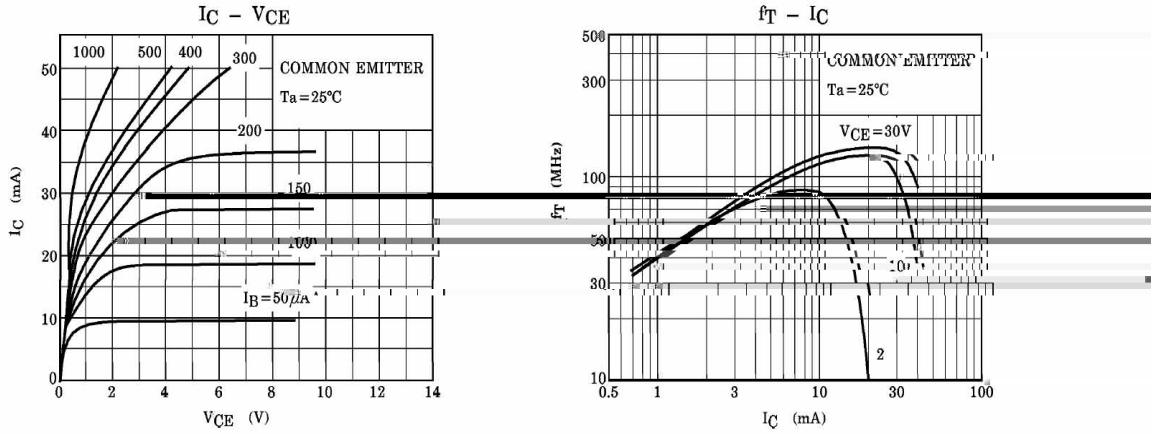
/ h_{FE} Classifications & Marking

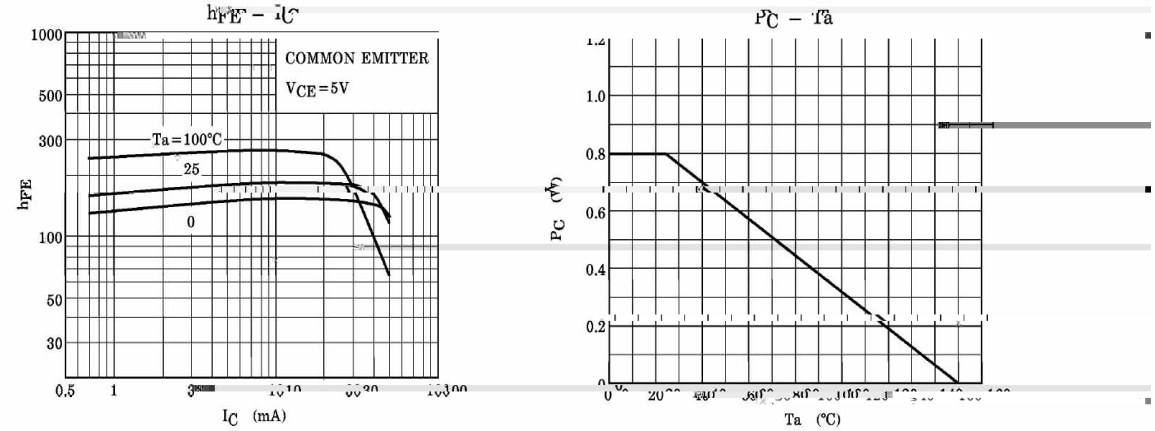
h_{FE} Classifications Symbol	O	Y
h_{FE} Range	70 140	120 240

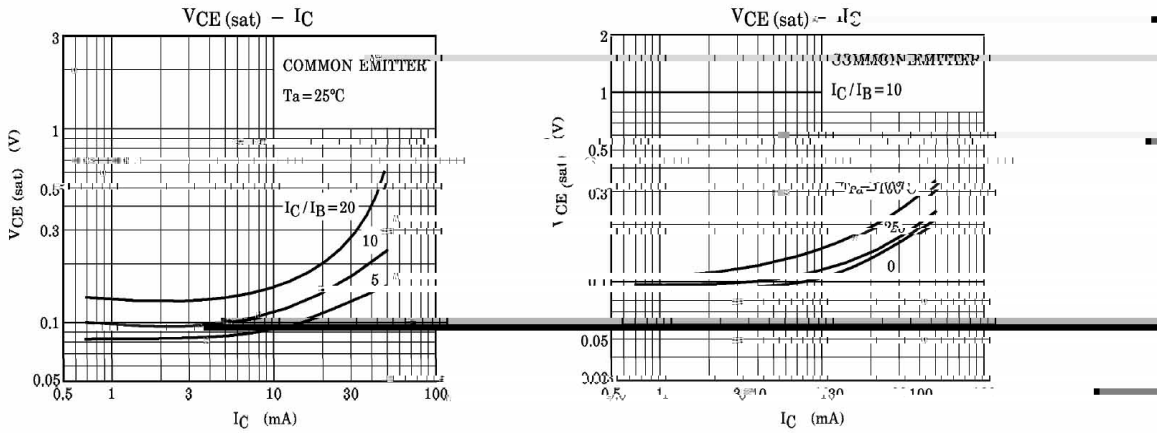
v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	150	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	50	mA
Emitter Current	I_E	-50	mA
Collector Power Dissipation	P_C	800	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ̈Ω Parameter	ϒ N Symbol	Ш :ϯ Ţ Test Conditions	ώ ή Ö Min	Ε ʒ Ö Typ	ώ ᶻ Ö Max	D Ч Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=200V I_E=0			0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			0.1	μA
DC Current Gain	h_{FE} FEC 0 7.02 238.56 394.40 399892003 Tc0 Tw6C					

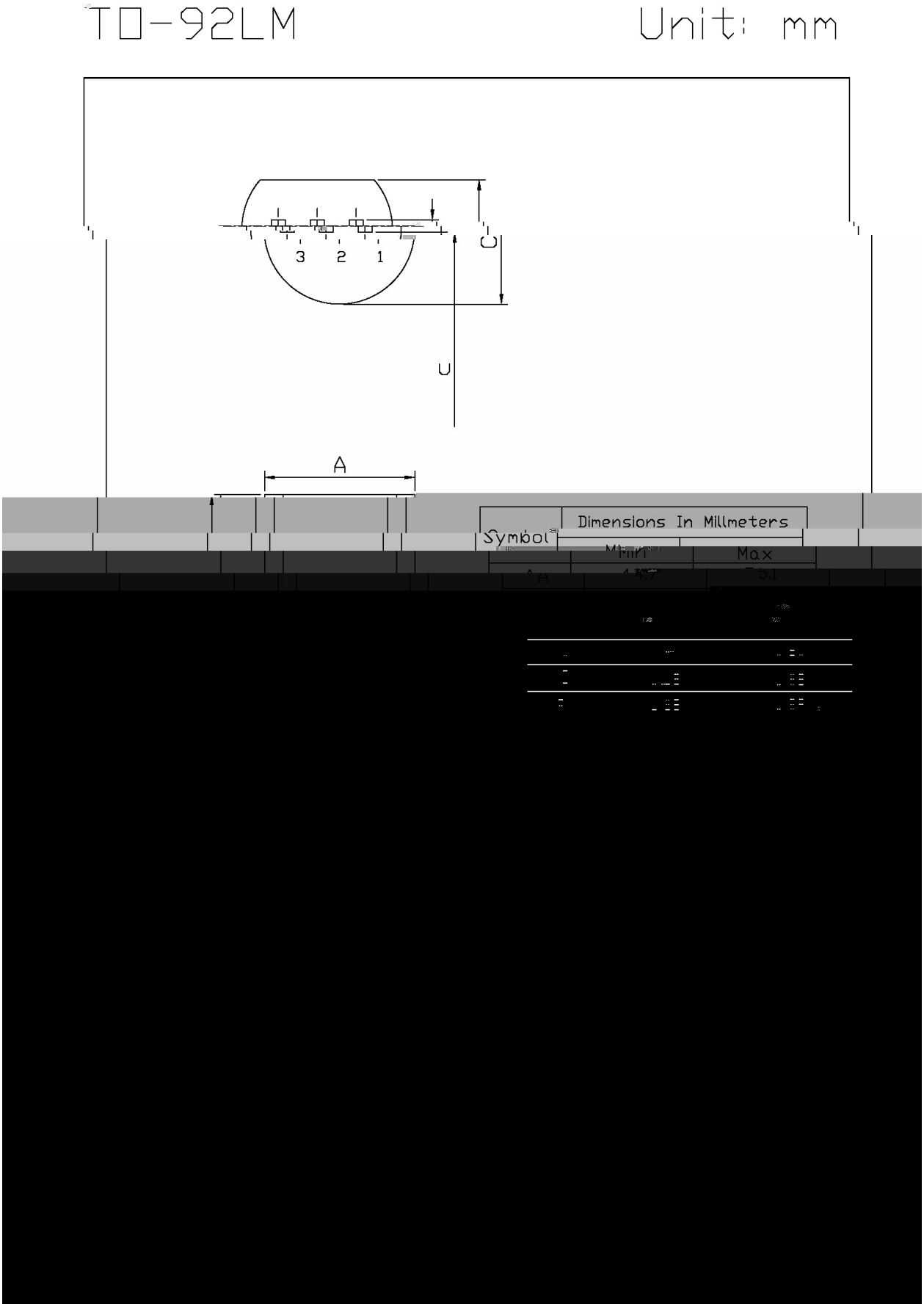
/ Electrical Characteristic Curve



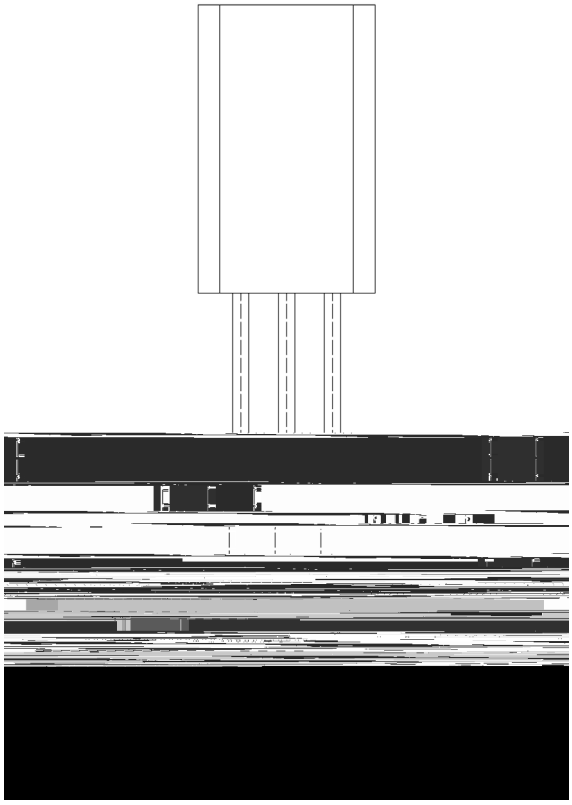




/ Package Dimensions



/ Marking Instructions

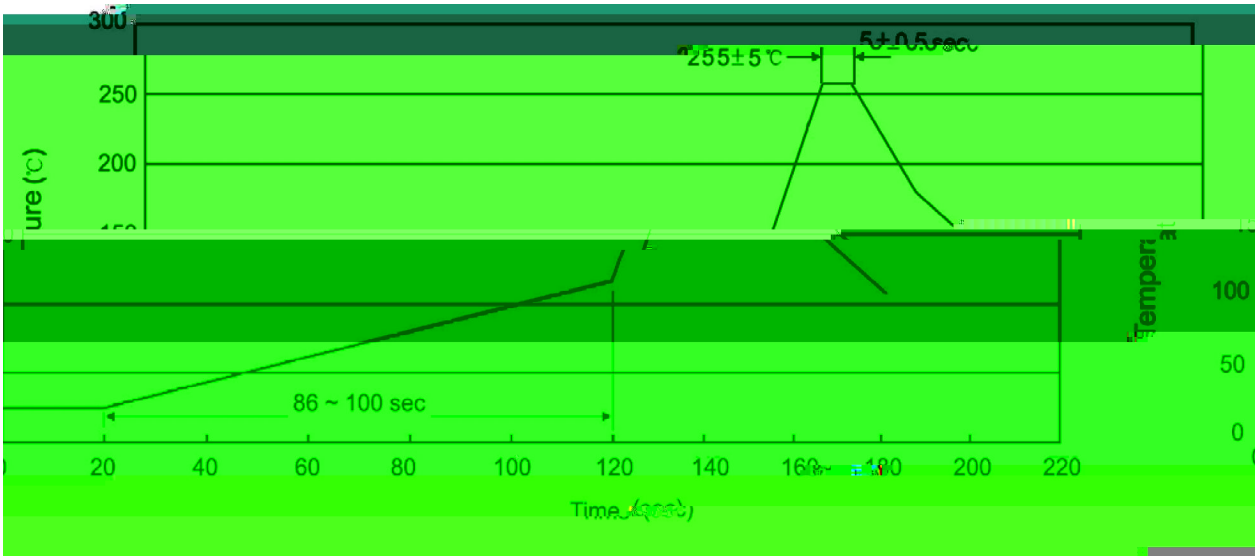


ᄂ ˝ χ

EU=

F555< χ

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı ˙H ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ł ı ˙H ڑ ˙Y ﾊ ㎛ 5 ° 0.5sec;

3 ì ˙ ﾘ ˛ ɔ ﻉ ỷ ㎛ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 270 ° 5 ł	˙H ڑ χ 10 ° 1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

˙Ω ţ ﾘ Ł / BULK